Central ** Semiconductor Corp.

145 Adams Avenue, Hauppauge, NY 11788 USA Tel: (631) 435-1110 • Fax: (631) 435-1824

Manufacturers of World Class Discrete Semiconductors

PN2221 PN2221A PN2222 PN2222A

NPN Silicon Transistor

JEDEC TO-92 Case

DESCRIPTION

The CENTRAL SEMICONDUCTOR PN2221,A,PN2222,A are Silicon NPN Planar Epitaxial Transistors designed for small signal general purpose and switching applications.

MAXIMUM RATINGS (TA=25°C unless	otherwise noted)	PN2221 PN2222	PN2221A PN2222A	
Collector-Base Voltage	Vсво	60	75	Vdc
Emitter-Base Voltage	VEBO	5.0	6.0	Vdc
Collector-Emitter Voltage	VCEO	30	40	Vdc
Collector Current-Continuous	10	800		mAdc
Power Dissipation	PŢ	625	mW	
Operating and Storage Junction Temperature	T _J ,T _{stg}	-65 TO +150		°C

ELECTRICA	L CHARACTERISTICS (TA=25°C)	PN2 PN2	222	PN2221A PN2222A	
Symbol	Test Conditions	Min	Max	Min Max	<u>Unit</u>
1CBO	V _{CB} =50V		10	4.0	nA
I CBO	VCB=60V			10	nA
ICEV	VCE=60V, VEB=3.0V			10	nA
1E80	VEB=3.0V		10	10	nA
BACBO	1 C=10uA	60		75	٧
BAEBO	IE=10uA	5.0		6.0	V
BVCEO .	$I_{C}=10mA$	30	- 1	40	٧
VCE(s)	IC=150mA, IB=15mA		0.4	0.3	V
VCE(s)	IC=500mA, IB=50mA		1.6	1.0	٧
VBE(s)	IC=150mA, IB=15mA		1.3	1.2	V
VBE(s)	IC=500mA, IB=50mA		2.6	2.0	V
		PN2		PN2222	
			221A	PN2222A	
		Min	Max	Min Max	<u>Unit</u>
hFE	VCE=10V, IC=100uA	20		35	-
hFE	VCE=10V, IC=1mA	25		50	-
hFE	VCE=10V, IC=10mA	35		75	-
hFE	VCE=10V, 1C=150mA	40	120	100 300	-
hFE	V _{CE} =1V, I _C =150mA	20		50	-
hFE	VCE=10V, IC=500mA(PN2221, PN2222 Only)	20		30	-
hFE	VCE=10V, IC=500mA(PN2221A,PN2222A Only)	25		40	-
fŢ	VCE=20V, IC=20mA,f=100MHz(Except PN22222	4) 250		250	MHz
fT	VCE=20V, IC=20mA, f=100MHz (PN2222A only)			300	MHz
€ _{ob}	V _{CB} =10V, f=100kHz		8.0	8.0	рF
tON	Vcc=30V, Ic=150mA, IB=15mA		35	35	ns
tOFF	Vcc=30V, Ic=150mA, IB1=IB2=15mA		285	285	ns

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